November 1999

ADVANCE INFORMATION



FDZ201N N-Channel 2.5V Specified PowerTrench[™] BGA MOSFET

General Description

FAIRCHILD

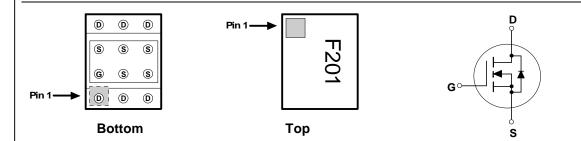
Combining Fairchild's advanced 2.5V specified PowerTrench process with state of the art BGA packaging, the FDZ201N minimizes both PCB space and $R_{DS(ON)}$. This BGA MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, high current handling capability, ultralow profile packaging, low gate charge, and low $R_{DS(ON)}$.

Applications

- Battery management
- Load switch
- Battery protection

Features

- 9 A, 20 V. $R_{DS(ON)} = 0.018 \ \Omega \ @ V_{GS} = 4.5 \ V$ $R_{DS(ON)} = 0.030 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Occupies only 5 mm² of PCB area. Only 55% of the area of SSOT-6
- Ultra-thin package: less than 0.70 mm height when mounted to PCB
- Outstanding thermal transfer characteristics: 4 times better than SSOT-6
- Ultra-low Q_g x R_{DS(ON)} figure-of-merit.
- High power and current handling capability.



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DSS}	Drain-Source Voltage			20	
V _{GSS}	Gate-Source	e Voltage		±12	V
I _D	Drain Currer	nt – Continuous	(Note 1a)	9	A
		– Pulsed		20	
P _D	Power Dissip	pation (Steady State)	(Note 1a)	2.7	W
	Operating and Storage Junction Temperature Range				
T _J , T _{stg}	Operating ar	nd Storage Junction Temp	erature Range	-55 to +175	°C
Therma	l Charact	eristics	 		
Therma R _{0JA}	I Charact	eristics sistance, Junction-to-Ambi	ent (Note 1a)	55	°C/W
<u> </u>	I Charact	eristics	ent (Note 1a)		
Therma R _{өJA} R _{өJC}	I Charact	eristics sistance, Junction-to-Ambi	ent (Note 1a) (Note 1)	55	°C/W
Therma _{Rөла} Rөлс Packag	I Charact	eristics sistance, Junction-to-Ambi sistance, Junction-to-Case	ent (Note 1a) (Note 1)	55	°C/W

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FDZ201N

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	20			V
$\Delta BV_{DSS} \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$		14		mV/°C
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I _{GSSF}	Gate–Body Leakage Current, Forward	$V_{GS} = 12 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	'nA
I _{GSSR}	Gate–Body Leakage Current, Reverse	$V_{GS} = -12 \text{ V} \qquad V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)	·				
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	0.4	0.9	1.5	V
R _{DS(on)}	Static Drain–Source On–Resistance				0.018 0.030	Ω
Drain-S	ource Diode Characteristics	and Maximum Ratings		•		
Is	Maximum Continuous Drain–Source Diode Forward Current				2.3	А
V _{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 2.3 A$ (Note 2)		0.77	1.2	V

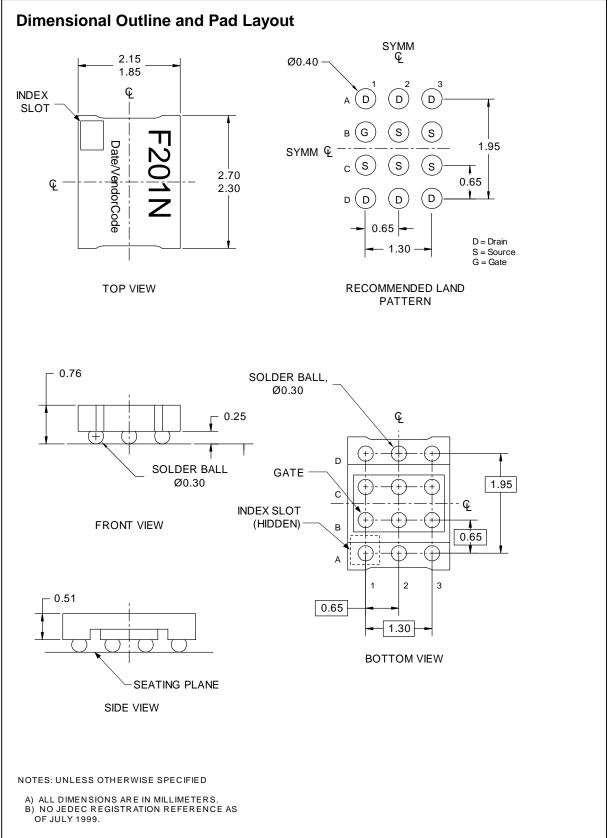
Notes:

1. $R_{\theta JA}$ is a function of the junction-to-case ($R_{\theta JC}$), case-to-ambient ($R_{\theta CA}$) and the PC Board ($R_{\theta BA}$) thermal resistance where the case thermal reference is defined the top surface of the package. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ and $R_{\theta BA}$ are determined by the user's design.

(a). $\rm R_{\theta JA}$ = 55°C/W (steady-state) when mounted on 1 in² of 2 oz. copper.

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

FDZ201N Rev A (W)



FDZ201N

FDZ201N Rev A (W)

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